



HBC558

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The HBC558 is designed for switching and AF amplifier amplification suitable for automatic insertion in thick and thin-film circuits.

Absolute Maximum Ratings

- Maximum Temperatures
Storage Temperature..... -55 ~ +150 °C
Junction Temperature..... +150 °C
- Maximum Power Dissipation
Total Power Dissipation ($T_A=25^{\circ}\text{C}$)..... 500 mW
- Maximum Voltages and Currents ($T_A=25^{\circ}\text{C}$)
 V_{CBO} Collector to Base Voltage -30 V
 V_{CEO} Collector to Emitter Voltage..... -30 V
 V_{EBO} Emitter to Base Voltage -5 V
 I_C Collector Current -100 mA

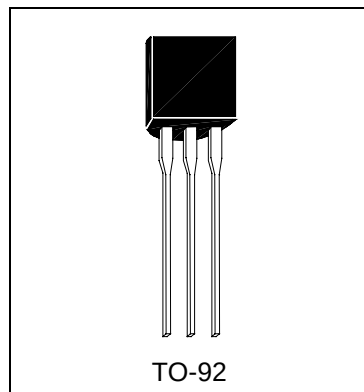
Electrical Characteristics ($T_A=25^{\circ}\text{C}$)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-30	-	-	V	$I_C=-100\mu\text{A}$
BV_{CEO}	-30	-	-	V	$I_C=-1\text{mA}$
BV_{EBO}	-5	-	-	V	$I_E=-10\mu\text{A}$
I_{CBO}	-	-	-15	nA	$V_{CB}=-30\text{V}$
$*V_{CE(sat)1}$	-	-90	-300	mV	$I_C=-10\text{mA}$, $I_B=-0.5\text{mA}$
$*V_{CE(sat)2}$	-	-250	-650	mV	$I_C=-100\text{mA}$, $I_B=-5\text{mA}$
$*V_{BE(sat)1}$	-	-700	-	mV	$I_C=-10\text{mA}$, $I_B=-0.5\text{mA}$
$*V_{BE(sat)2}$	-	-900	-	mV	$I_C=-100\text{mA}$, $I_B=-5\text{mA}$
$V_{BE(on)1}$	-600	-	-750	mV	$V_{CE}=-5\text{V}$, $I_B=-2\text{mA}$
$V_{BE(on)2}$	-	-	-800	mV	$V_{CE}=-5\text{V}$, $I_B=-10\text{mA}$
$*h_{FE}$	110	-	800		$V_{CE}=-5\text{V}$, $I_C=-2\text{mA}$
f_T	-	150	-	MHz	$V_{CE}=-5\text{V}$, $I_C=-10\text{mA}$
Cob	-	-	6	pF	$V_{CB}=-10\text{V}$, $f=1\text{MHz}$

*Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

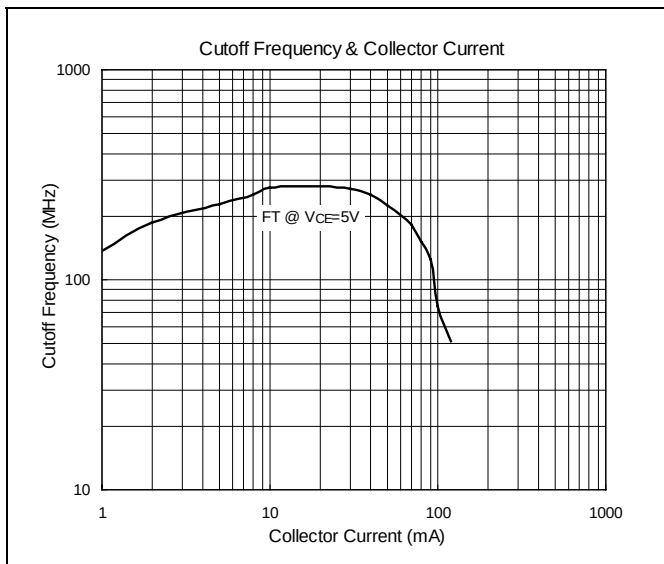
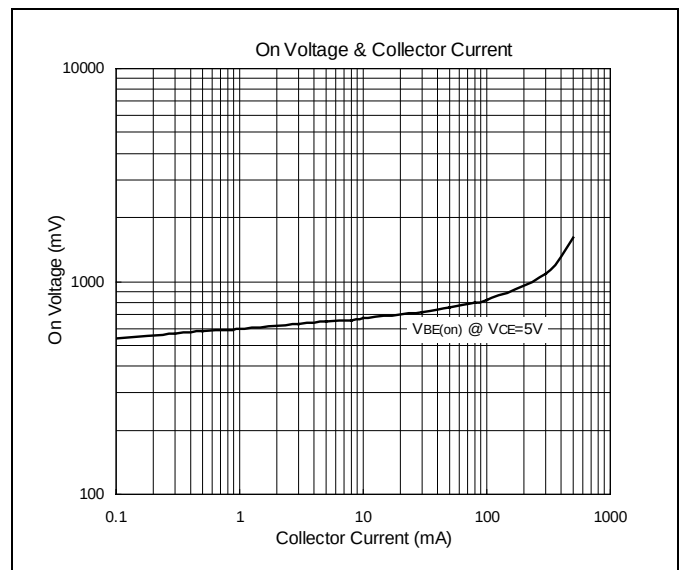
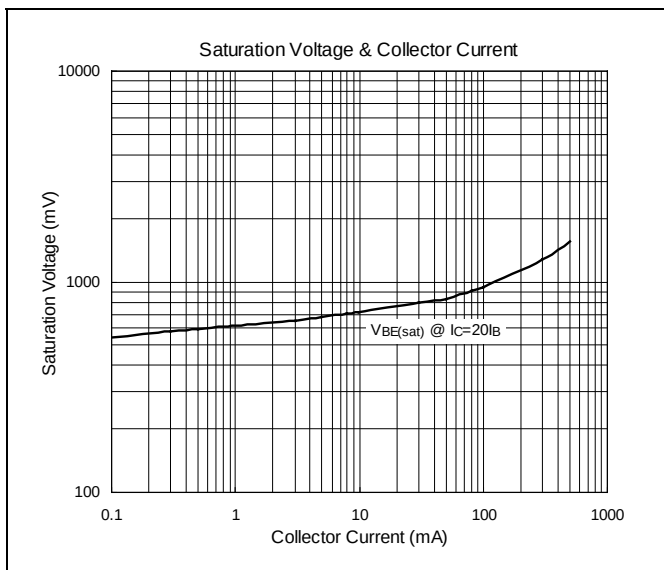
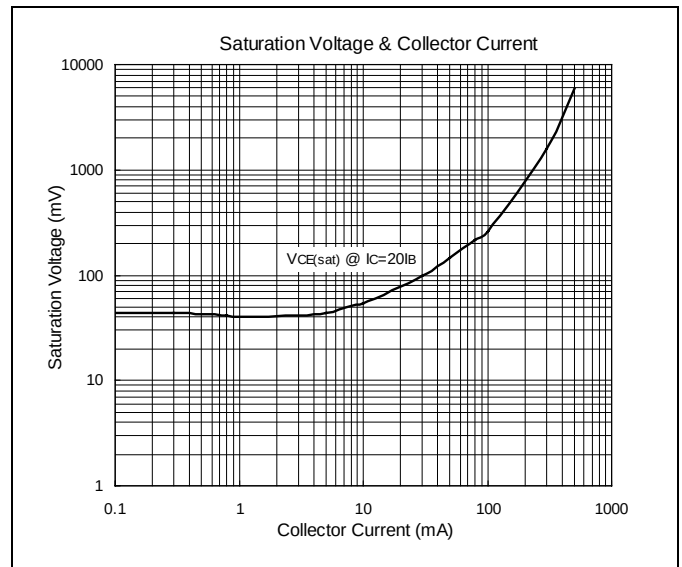
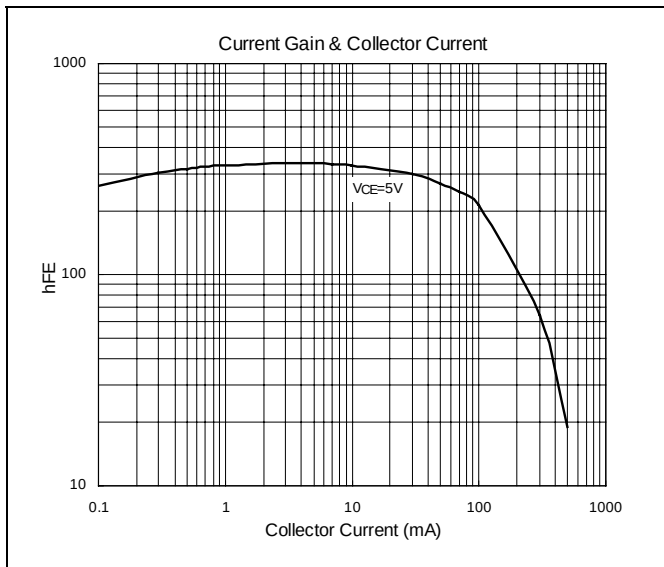
Classification Of hFE

Rank	A	B	C
hFE	110-220	200-450	420-800



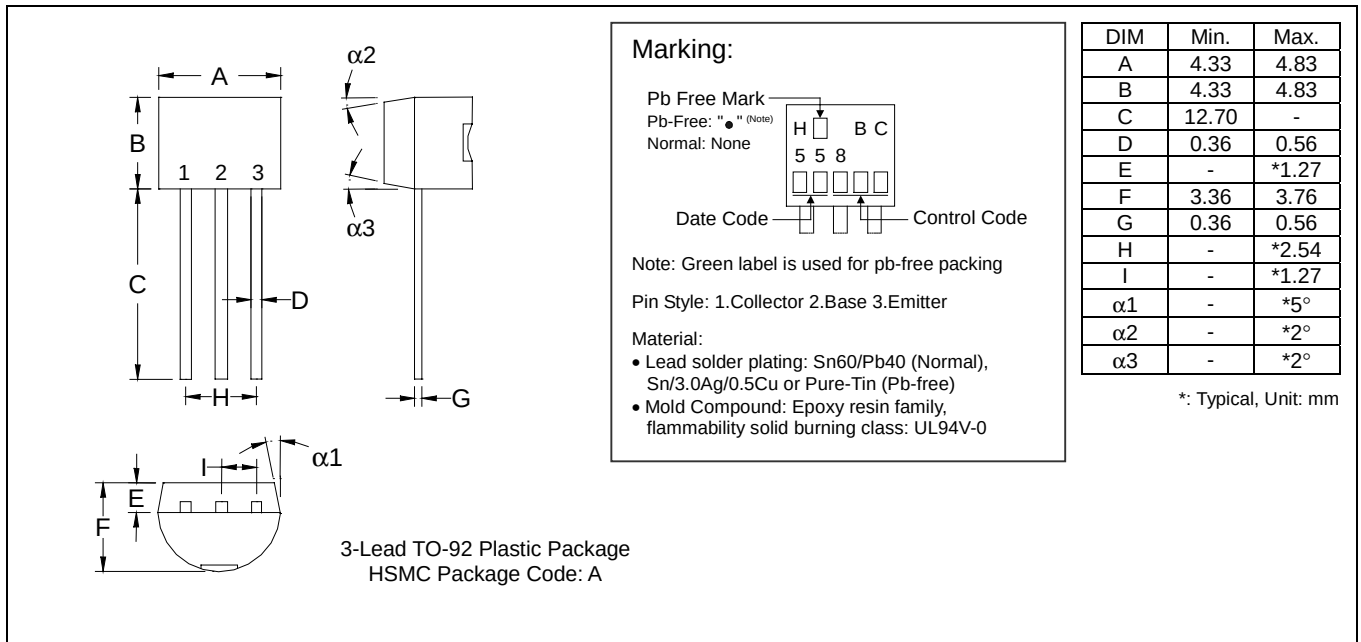


Characteristics Curve

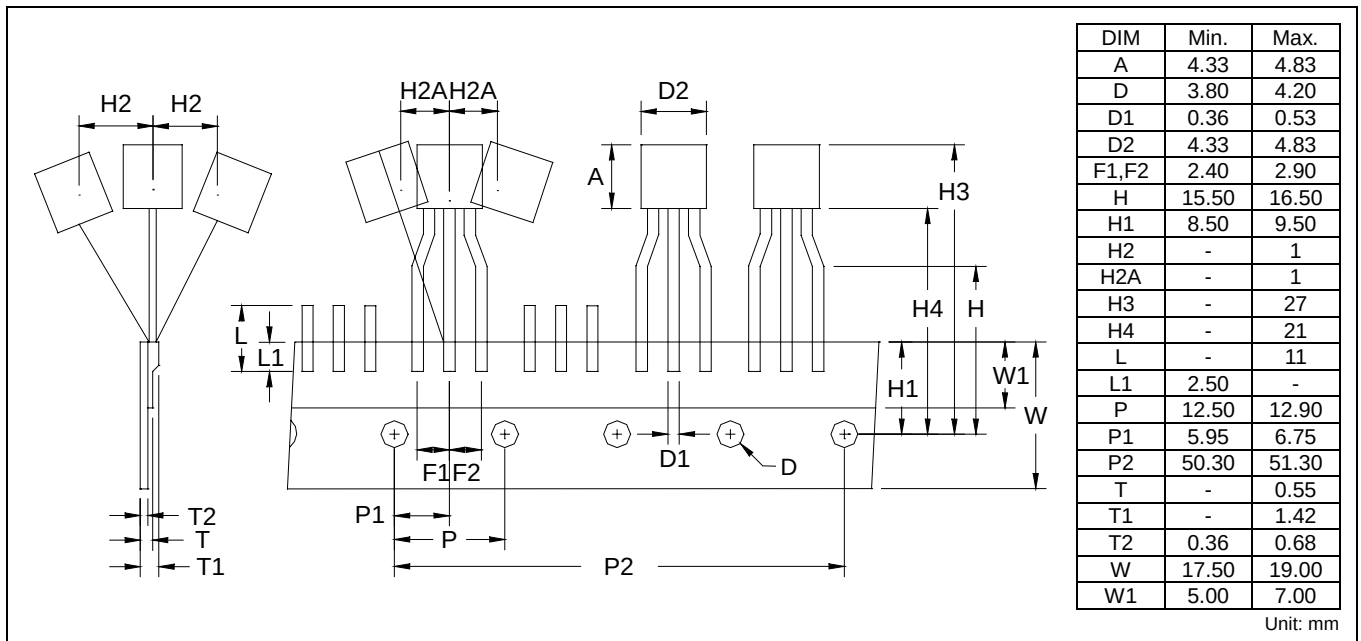




TO-92 Dimension



TO-92 Taping Dimension



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Head Office And Factory:

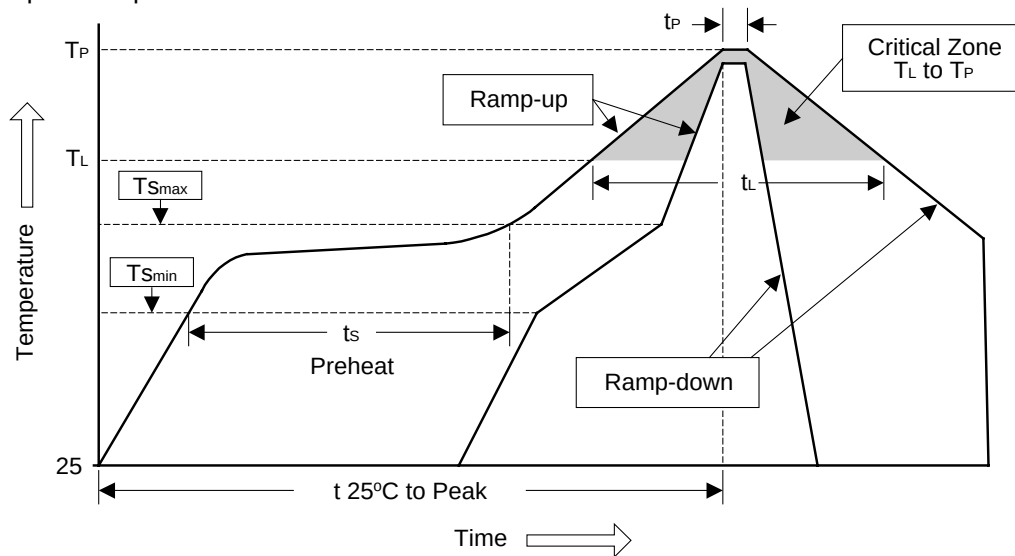
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Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{Smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec